

Description

The IRF540N uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gat e charge. It can be used in a wide variety of applications.

S G

TO-220 (TO-220AB)

General Features

 $V_{DS} = 100V, I_{D} = 33A$

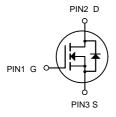
 $R_{DS(ON)} < 38m \Omega$ @ $V_{GS}=10V$

Application

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Units Tube
IRF540N	TO-220(TO-220AB)	HXY IRF540N YYYY	50

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I _D @T _C =25°C	Drain Current	33	Α
IDM	Pulsed Drain Current ¹	120	Α
P _D @T _C =25°C	Total Power Dissipation	130	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	℃



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage (Note 1)	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	-	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	-	30	38	mΩ
Forward Transconductance	g _{FS}	g _{FS} V _{DS} =10V,I _D =20A		-	-	S
Dynamic Characteristics			•			
Input Capacitance	C _{lss}	\/ -50\/\/ -0\/	-	1280	-	PF
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V, F=1.0MHz	-	300	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0IVInz	-	26	-	PF
Switching Characteristics			•			
Turn-on Delay Time	t _{d(on)}		-	12	-	nS
Turn-on Rise Time	t _r	$V_{DD} = 50V, I_{D} = 15A$	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}	R_G =4.7 Ω (Note 2)	-	23	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg	V 50VI 20A	-	20	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=50V,I_{D}=30A,$ $V_{GS}=10V^{(Note 2)}$	-	10	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} = IUV	-	5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =15A	-		1.4	V
Diode Forward Current (Note 2)	Is		-	-	33	Α

Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

^{2.} Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.



Typical Electrical

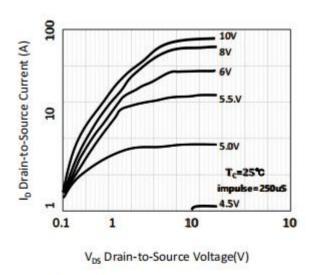


Figure 1. Typical Output Characteristics

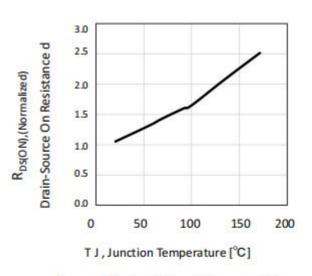
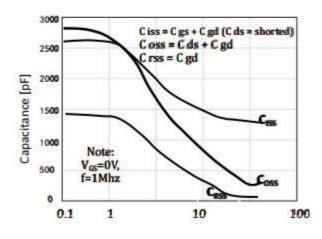


Figure 2. Typical Output Characteristics



V_{DS} Drain-to-Source Voltage (V)

Figure 3. Typical Capacitance Vs Drain-Source Voltage

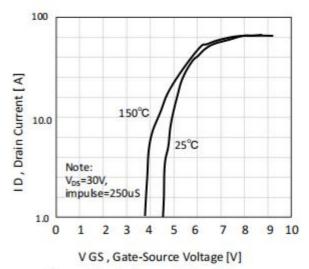
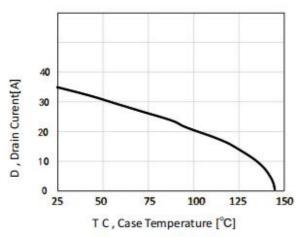


Figure 4. On-Resistance Vs Drain Current



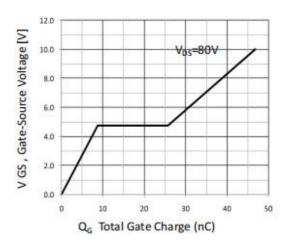


Figure 5. Maximum Drain Current Vs Temperature

Figure 6. Typical Gate Charge Vs Gate-Source Voltage

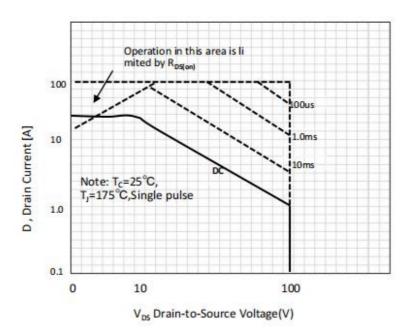
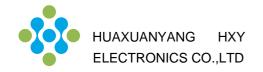
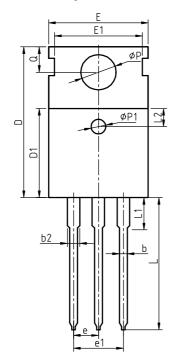
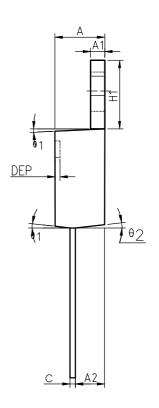


Figure 7. Maximum Safe Operating Area



Package Information TO-220(TO-220AB)





COMMON DIMENSIONS



SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
Α	4.40	4.57	4.70	0. 173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1. 27	1.36	0.046	0.050	0.054
С	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9. 10	9. 20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
Ε	9.80	10.00	10.20	0. 386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
е		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0. 252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
Р	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0. 107	0.110	0. 113
θ 1	5°	7°	9°	5°	7°	9°
θ 2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°

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